

removing the semiconductor wafer from a polishing plate;

immediately after removing the semiconductor wafer from the polishing plate, bringing the semiconductor wafer into contact with an aqueous treatment agent solution for oxidizing a polished surface of the semiconductor wafer by action of the aqueous treatment agent solution,

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the wafer being brought into contact with the aqueous treatment agent solution in a manner which is selected from the group consisting of (a) spraying the semiconductor wafer with the aqueous treatment agent solution, (b) dipping the semiconductor wafer into the aqueous treatment agent solution and (c) applying the aqueous treatment agent solution to the polished surface of the semiconductor wafer by means of a cloth which has been moistened with the aqueous treatment agent solution; and cleaning the semiconductor wafer.

17. (Amended) Process for treating a semiconductor wafer, comprising

polishing the semiconductor wafer;

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immediately after polishing the semiconductor wafer removing the semiconductor wafer from a polishing plate;

immediately after removing the semiconductor wafer from the polishing plate, bringing the semiconductor wafer into contact with an aqueous treatment agent solution for oxidizing a polished surface of the semiconductor wafer by action of the aqueous treatment agent solution,

the wafer being brought into contact with the aqueous treatment agent solution in a manner which is selected from the group consisting of (a) spraying the semiconductor wafer with the aqueous treatment agent solution, (b) dipping the semiconductor wafer into the aqueous treatment agent solution and (c) applying the aqueous treatment agent solution to the polished surface of the semiconductor wafer by means of a cloth which has been moistened with the aqueous treatment agent solution;

flushing the treatment agent solution off the semiconductor wafer by using deionized water, after completing the oxidizing; and

cleaning the semiconductor wafer.

18. (Amended) Process for treating a semiconductor wafer, comprising

polishing the semiconductor wafer;

immediately after polishing the semiconductor wafer removing the semiconductor wafer from a polishing plate;

immediately after removing the semiconductor wafer from the polishing plate, bringing the semiconductor wafer into contact with an aqueous treatment agent solution for oxidizing a polished surface of the semiconductor wafer by action of the aqueous treatment agent solution,

the wafer being brought into contact with the aqueous treatment agent solution in a manner which is selected from the group consisting of (a) spraying the semiconductor wafer with the

aqueous treatment agent solution, (b) dipping the semiconductor wafer into the aqueous treatment agent solution and (c) applying the aqueous treatment agent solution to the polished surface of the semiconductor wafer by means of a cloth which has been moistened with the aqueous treatment agent solution;

wherein the aqueous treatment agent solution comprises an aqueous solution of

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- (1) from 0.02% to 3.0% by volume, based upon the total solution volume, of an oxidizing agent which is hydrogen peroxide;
 - (2) from 0.01% to 2.0% by weight, based upon the total solution weight, of an alkaline component; and
 - (3) the balance up to 100% by volume being water based upon the total solution volume, and the balance up to 100% by weight being water, which is based upon the total solution weight;

wherein the alkaline component is selected from the group consisting of tetramethylammonium hydroxide, ammonium hydroxide, potassium hydroxide, sodium hydroxide, potassium carbonate and the mixtures thereof; and
cleaning the semiconductor wafer.

REMARKS

Reconsideration of this patent application is respectfully requested in view of the foregoing amendments, and the following